

Application No. 10/700,429  
Reply to Office Action of July 11, 2005  
Amendment dated January 11, 2006

Amendments to the Specification

~~Please replace the paragraph that was inserted~~  
before the first line of the specification with the following <sup>YK 1/21/2010</sup>  
~~amended version of that paragraph:~~

This application is a continuation of copending,  
commonly assigned United States Patent Application  
No. 09/775,597, filed February 5, 2001, now U.S. Patent  
No. 6,682,981, which is a continuation of United States  
Patent Application No. 09/027,959, filed February 23, 1998,  
now abandoned, which is a division of United States Patent  
Application No. 08/850,749, filed May 2, 1997, now U.S.  
Patent No. 5,985,693, which is a continuation of United  
States Patent Application No. 08/315,905, filed September 30,  
1994, now U.S. Patent No. 5,869,354, which is a division of  
United States Patent Application No. 07/865,412, filed April  
8, 1992, now U.S. Patent No. 5,354,695, all of which are  
incorporated by reference herein in their entireties.

Please replace the paragraph at page 24,  
lines 10-34 with the following amended version of that  
paragraph:

The Air Tunnel structure in one embodiment is  
fabricated with CVD processing techniques; alternatively, ECR  
(Electron-Cyclotron-Resonance) plasma CVD processing may soon  
provide an alternative deposition method. The gaseous  
dielectric separation of a conductor or a semiconductor  
device is accomplished by forming a sacrificial CVD film of  
a-Si, polysilicon or alternate material (typically dielectric  
material) that can be deposited by CVD means and selectively  
etched versus the other MDI circuit membrane material layers.